GaAs LIGHT-EMITTING DIODE
62033 (TYPE GS 5040)

OPTOELECTRONIC PRODUCTS DIVISION

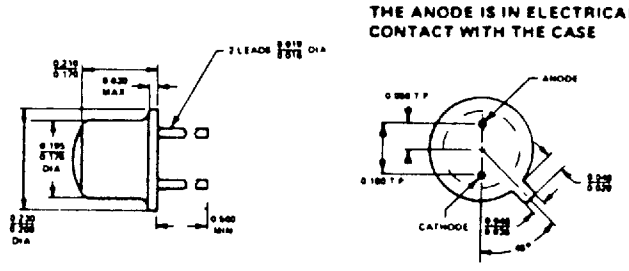
T-41-11

*** HIGH INTENSITY GaAlAs VERSION AVAILABLE**

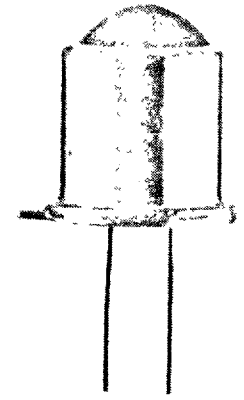
RECESSED TO-46 HEADER FOR PRECISE BEAM ALIGNMENT
HIGH EFFICIENCY
HERMETIC PACKAGE

Mii 62033 is a P-N GaAs Infrared Light Emitting Diode in a lensed TO-46 package, and is spectrally matched to silicon sensors. Available screened to MIL-S-19500.

PHYSICAL DESCRIPTION



ALL DIMENSIONS ARE IN INCHES UNLESS OTHERWISE SPECIFIED



OPTICAL/ELECTRICAL CHARACTERISTICS AT 25°C

PARAMETER	OPTICAL POWER		FORWARD DROP	REVERSE BREAKDOWN	RADIATION RISE TIME	PEAK WAVELENGTH	BEAM ANGLE	FWD CURRENT CONTINUOUS
TEST CONDITION	I_F = 100mA		I_F = 100mA	I_R = 10 µA		I_F = 100mA	Note 1	25 C Case
SYMBOL	P_O		V_F	BV_R	t_r	λP	"	I_F
UNIT	mW		VOLTS	VOLTS	µ sec	nm	degrees	mA
	MIN	TYP	MAX	MIN	TYP	TYP	TYP	MAX
GS 5040-1	2.0	2.5	1.7	2.0	0.7	940	20	200
GS 5040-2	3.5	4.2	1.7	2.0	0.7	940	20	200
GS 5040-3	4.8	6.0	1.7	2.0	0.7	940	20	200

1 Angle between half intensity points

* Contact factory for 62050

Ga As LIGHT-EMITTING DIODE, TYPE GS 5040, *Continued*

62033 LIGHT-EMITTING DIODE

ABSOLUTE MAXIMUM RATINGS 25°C FREE AIR TEMPERATURE UNLESS NOTED

Reverse Voltage at 25°C Case Temperature	2 V
Continous Forward Current at 25°C Case Temperature (See Note)	200 mA
Operating Case Temperature Range	-40°C to 80° C
Storage Temperature Range	-40°C to 100° C
Soldering Temperature 1/16 inch From Case for 10 Seconds	240° C

NOTE: derate linearly to 80°C case temperature at the rate of 3.6 mA/°C

TYPICAL CHARACTERISTICS